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Honeywell's Docket No. 30-4790 (4780)  
Practitioner's Docket No. 595.048-US3

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: ZHANG, et al.

09/357,264

Application No.: 09/357,234

Group No.: 1765

Filed: July 19, 1999

Examiner: Charlotte A. Brown

For: COMPOSITION FOR CHEMICAL MECHANICAL PLANARIZATION OF COPPER,  
TANTALUM AND TANTALUM NITRIDE

RECEIVED

NOV 28 2001

TC 1700

Box CPA (RCE)

Assistant Commissioner for Patents

Washington, D.C. 20231

REQUEST FOR CONTINUED EXAMINATION (RCE)  
(37 C.F.R. 1.114)

1. Applicant hereby requests continued examination, in accordance with 37 C.F.R. Section 1.114, for the above identified application.

CERTIFICATION UNDER 37 C.F.R. SECTIONS 1.8(a) AND 1.10

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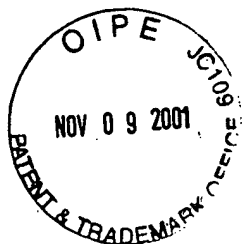
Kristin J. Azcona

11/26/2001 HVDW61 00000025 09357234

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(Request for Continued Examination (RCE))--page 1 of 3)



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE  
WASHINGTON, D.C. 20231

Inventor: **Zhang et al.**

Serial No: **09/357234**

Filed: **July 19, 1999**

For: **Comp. for Chemical Mechanical  
Planarization of Copper,  
Tantalum and Tantalum Nitride**

Examiner: Brown, Charlotte A.

Art Unit: 1765

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**PRELIMINARY AMENDMENT**

The Honorable Commissioner  
of Patents and Trademarks  
Washington, D.C. 20231

Dear Sir:

1. (Amended) [In a] A chemical mechanical planarization system that includes a Cu/Ta/TaN surface, a [replacement] single-step [etching] slurry solution comprising:
  - a) an oxidizing reactant selected from the group consisting of H<sub>2</sub>O<sub>2</sub>, HNO<sub>3</sub> and mixtures thereof; and
  - b) a co-reactant is selected from the group consisting of H<sub>3</sub>PO<sub>4</sub>, H<sub>2</sub>SO<sub>4</sub>, HNO<sub>3</sub>, oxalic acid, acetic acid, organic acids and mixtures thereof.
12. (Amended) The [etching] slurry solution of, claim 1 further comprising abrasive particles selected from the group consisting SiO<sub>2</sub>, Al<sub>2</sub>O<sub>3</sub> metallic and solid elemental particles, polymer particles, oxides, carbides, fluorides, carbonates, borides, nitrides, hydroxides of Al, Ag, Au, Ca, Ce, Cr, Cu, Fe, Gd, Ge, La, In, Hf, Mn, Ng, Ni, Nd, Pb, Pt, P, Sb, Sc, Sn, Tb, Ti, Ta, Th, Y, W, Zn, Zr, and mixtures thereof.